

isc Silicon NPN Power Transistors

2SB1261-K

DESCRIPTION

- Low Collector Saturation Voltage
- · High Power Dissipation-
 - : P_C= 10W(Max)@T_C=25°C
- Complement to Type 2SD1899-K
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

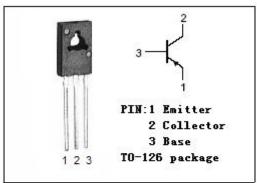


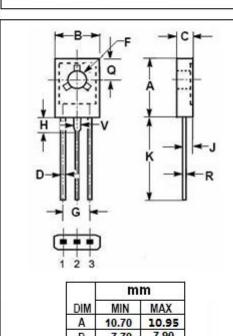
APPLICATIONS

 Designed for use in audio amplifier and switching, especially in hybrid integrated circuits.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|--------------|
| V _{CBO} | Collector-Base Voltage | -60 | V |
| V _{CEO} | Collector-Emitter Voltage | -60 | ٧ |
| V _{EBO} | Emitter-Base Voltage | -7 | V |
| Ic | Collector Current-Continuous | -3 | Α |
| Pc | Collector Power Dissipation @T _C =25°C | 10 | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ C |
| T _{stg} | Storage Temperature | -55~150 | $^{\circ}$ C |





| | mm | | |
|-----|-------|-------|--|
| DIM | MIN | MAX | |
| Α | 10.70 | 10.95 | |
| В | 7.70 | 7.90 | |
| С | 2.60 | 2.80 | |
| D | 0.66 | 0.86 | |
| F | 3.10 | 3.30 | |
| G | 4.48 | 4.68 | |
| н | 2.00 | 2.20 | |
| J | 1.35 | 1.55 | |
| K | 15.30 | 16.30 | |
| Q | 3.70 | 3.90 | |
| R | 0.40 | 0.60 | |
| V | 1.17 | 1.37 | |



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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|------|------|
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = -100 μ A ; I _E = 0 | -60 | | | V |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = -1mA ; I _B = 0 | -60 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown VItage | I _E = -100 μ A; I _C = 0 | -7 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -1.5A; I _B = -0.15A | | | -0.3 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = -1.5A; I _B = -0.15A | | | -1.2 | V |
| Ісво | Collector Cutoff Current | V _{CB} = -60V; I _E = 0 | | | -10 | μА |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -7V; I _C = 0 | | | -10 | μА |
| h _{FE1} | DC Current Gain | I _C = -0.2A; V _{CE} = -2V | 60 | | | |
| h _{FE} | DC Current Gain | I _C = -0.6A; V _{CE} = -2V | 200 | | 400 | |
| h _{FE} | DC Current Gain | I _C = -2A; V _{CE} = -2V | 50 | | | |

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